

# BF721T1

Preferred Device

## PNP Silicon Transistor

### Features

- Pb-Free Package is Available

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–300	Vdc
Collector–Base Voltage	$V_{CBO}$	–300	Vdc
Collector–Emitter Voltage	$V_{CER}$	–300	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current	$I_C$	–100	mAdc
Total Power Dissipation up to $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	1.5	W
Storage Temperature Range	$T_{stg}$	–65 to +150	$^\circ\text{C}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

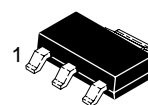
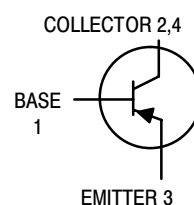
- Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in<sup>2</sup>.



ON Semiconductor®

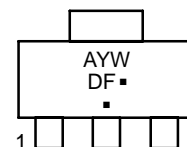
<http://onsemi.com>

## PNP SILICON TRANSISTOR SURFACE MOUNT



SOT-223 (TO-261)  
CASE 318E  
STYLE 1

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
DF = Device Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
BF721T1	SOT-223	1000 / Tape & Reel
BF721T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# BF721T1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-300	-	V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = -100 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-300	-	V <sub>dc</sub>
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -100 μA <sub>dc</sub> , R <sub>BE</sub> = 2.7 kΩ)	V <sub>(BR)CER</sub>	-300	-	V <sub>dc</sub>
Emitter-Base Breakdown Voltage (I <sub>E</sub> = -10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	V <sub>dc</sub>
Collector-Base Cutoff Current (V <sub>CB</sub> = -200 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-10	nA <sub>dc</sub>
Collector-Emitter Cutoff Current (V <sub>CE</sub> = -250 V <sub>dc</sub> , R <sub>BE</sub> = 2.7 kΩ) (V <sub>CE</sub> = -200 V <sub>dc</sub> , R <sub>BE</sub> = 2.7 kΩ, T <sub>J</sub> = 150°C)	I <sub>CER</sub>	-	-50 -10	nA <sub>dc</sub> μA <sub>dc</sub>
<b>ON CHARACTERISTICS</b>				
DC Current Gain (V <sub>CE</sub> = -25 mA <sub>dc</sub> , V <sub>CE</sub> = -20 V <sub>dc</sub> )	h <sub>FE</sub>	50	-	-
Collector-Emitter Saturation Voltage (I <sub>C</sub> = -30 mA <sub>dc</sub> , I <sub>B</sub> = -5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	-	-0.8	V <sub>dc</sub>
<b>DYNAMIC CHARACTERISTICS</b>				
Current-Gain – Bandwidth Product (V <sub>CE</sub> = -10 V <sub>dc</sub> , I <sub>C</sub> = -10 mA <sub>dc</sub> , f = 35 MHz)	f <sub>T</sub>	60	-	MHz
Feedback Capacitance (V <sub>CE</sub> = -30 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>re</sub>	-	1.6	pF

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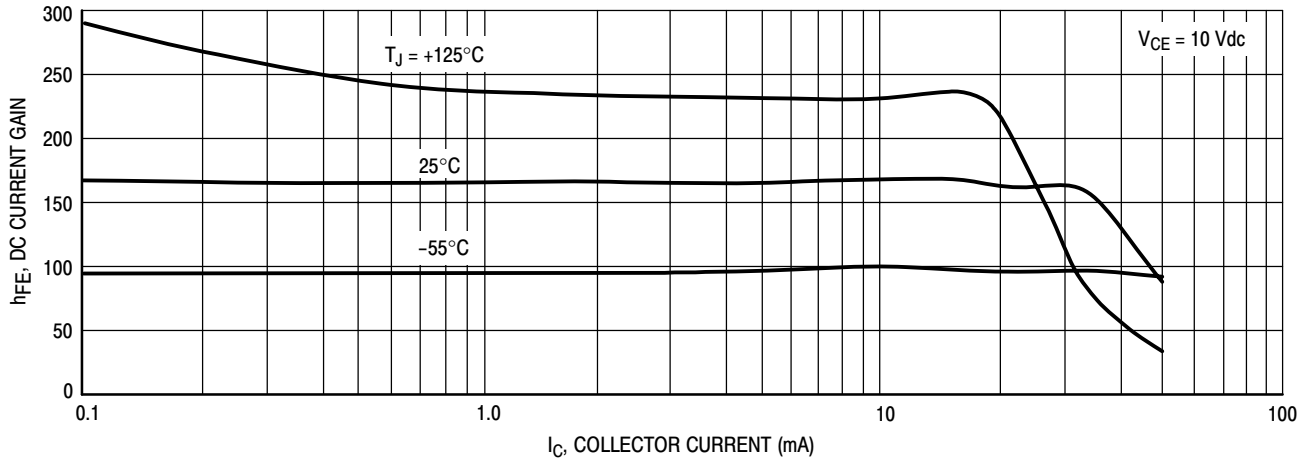


Figure 1. DC Current Gain

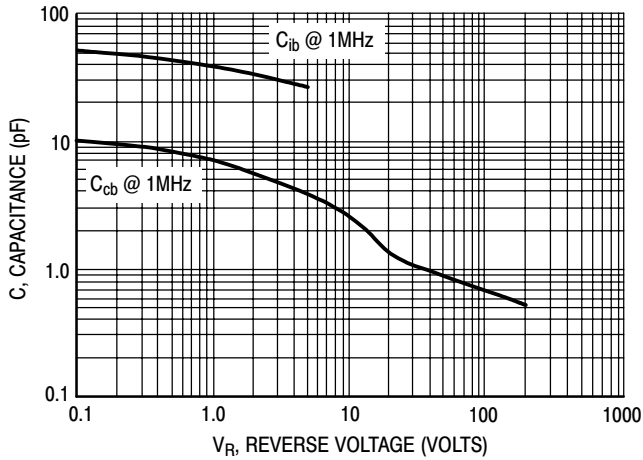


Figure 2. Capacitance

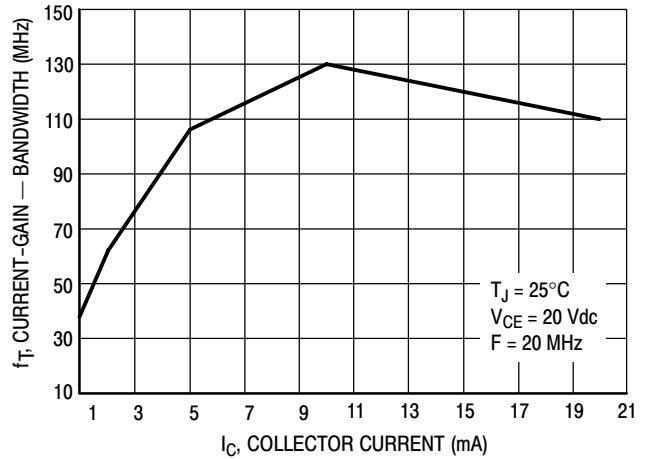


Figure 3. Current-Gain — Bandwidth

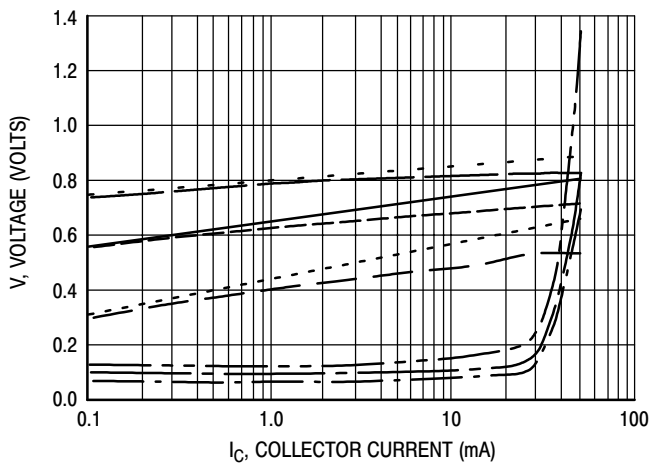


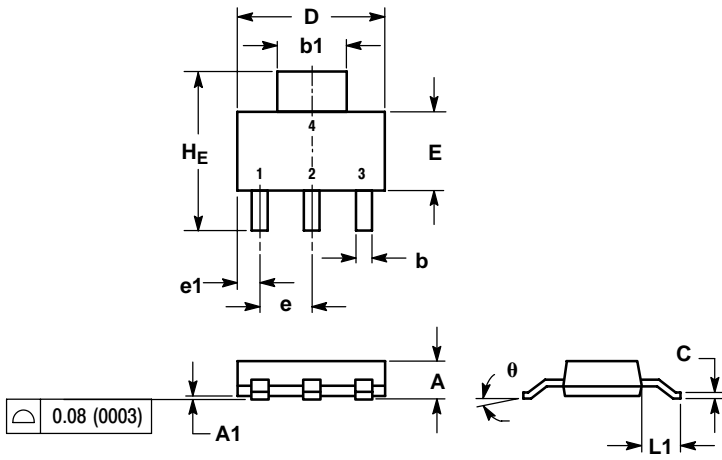
Figure 4. "ON" Voltages

- $V_{CE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- - -  $V_{BE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- - -  $V_{BE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(on)}$  @  $25^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- - -  $V_{BE(on)}$  @  $125^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$
- - -  $V_{BE(on)}$  @  $-55^\circ\text{C}$ ,  $V_{CE} = 10 \text{ V}$

# BF721T1

## PACKAGE DIMENSIONS

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE L



NOTES:

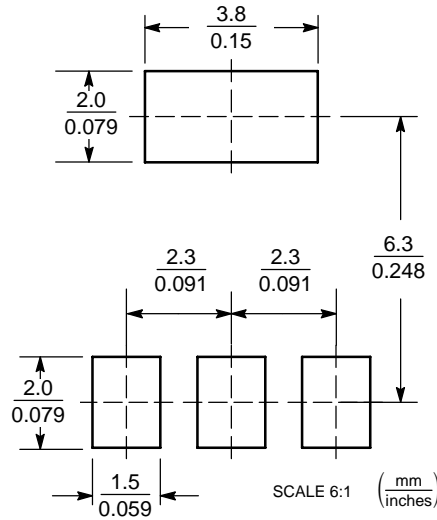
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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